

Fig. 1

(PRIOR ART)

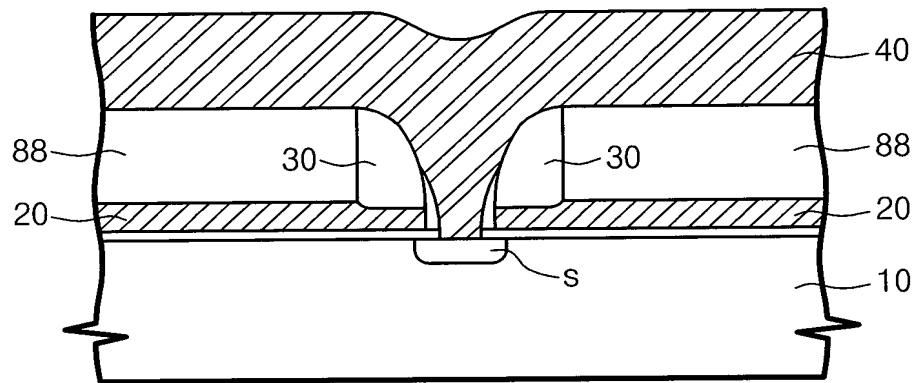


Fig. 2

(PRIOR ART)

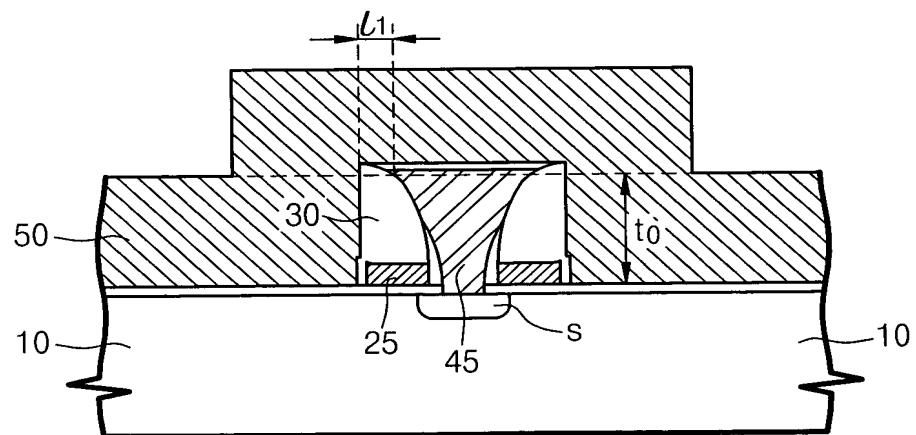


Fig. 3

(PRIOR ART)

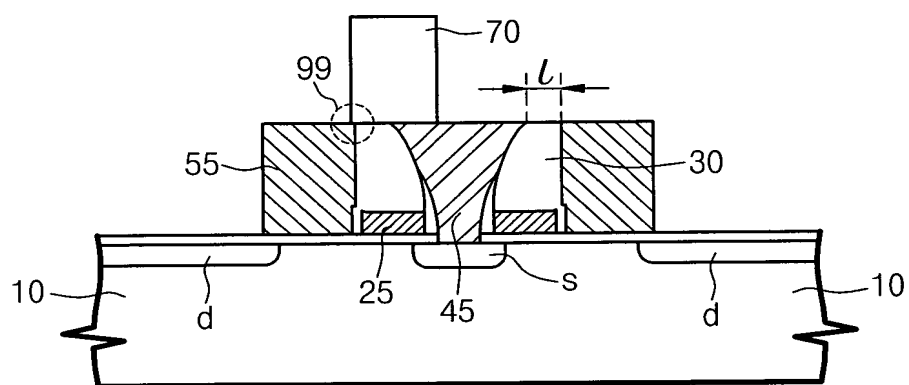


Fig. 4

(PRIOR ART)

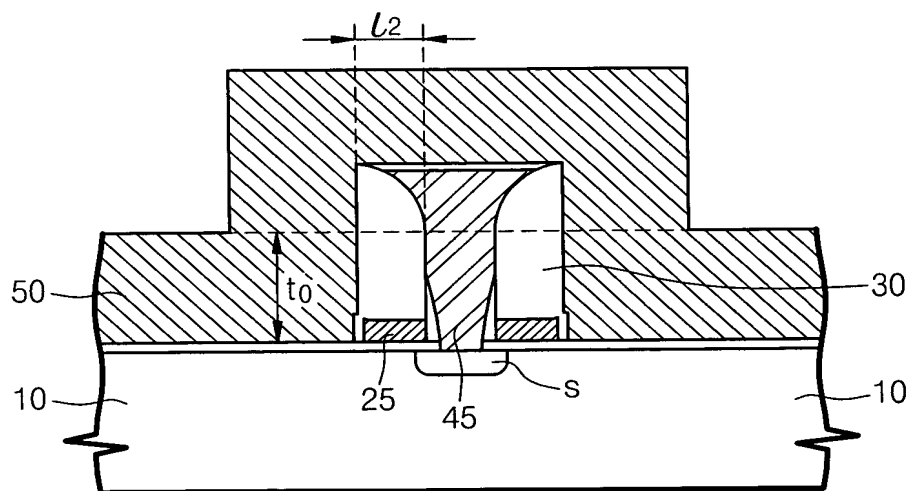


Fig. 5

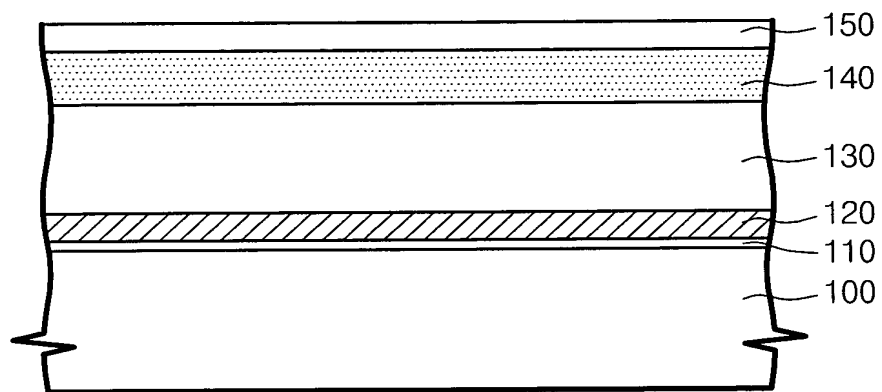


Fig. 6

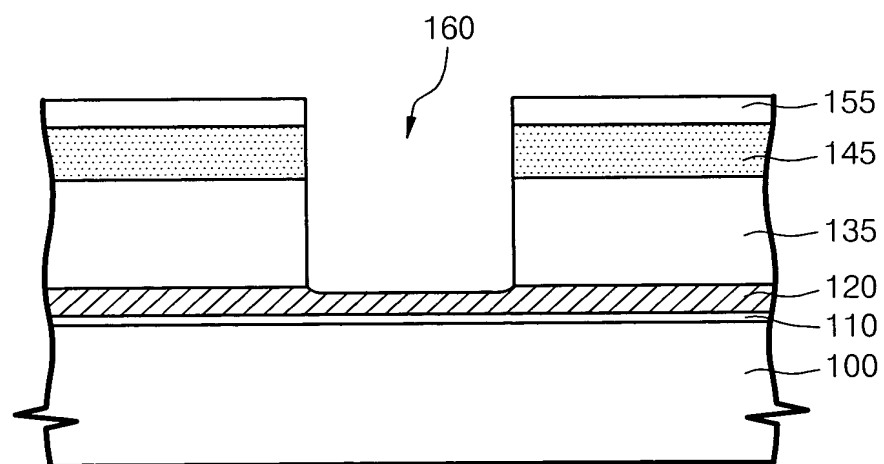


Fig. 7

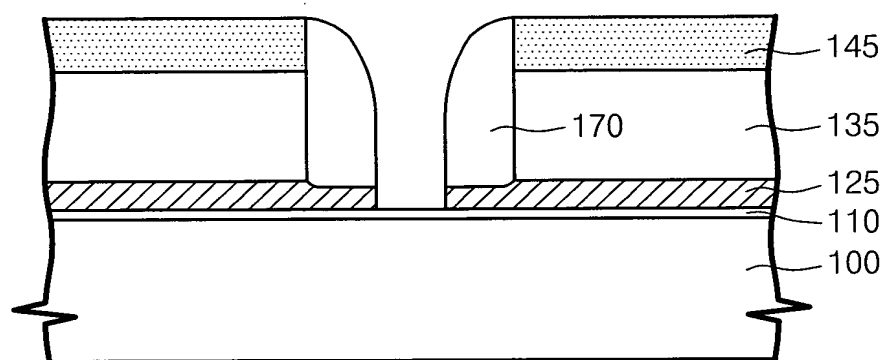
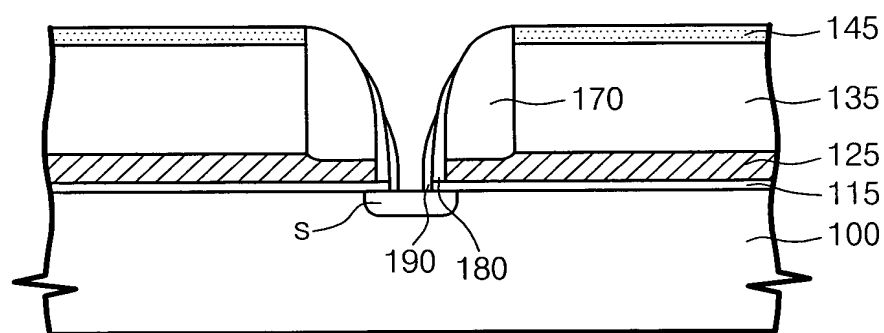


Fig. 8



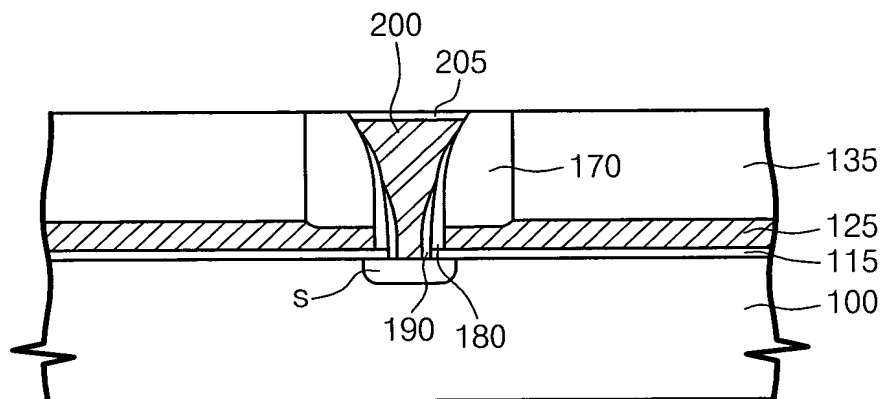


Fig. 10

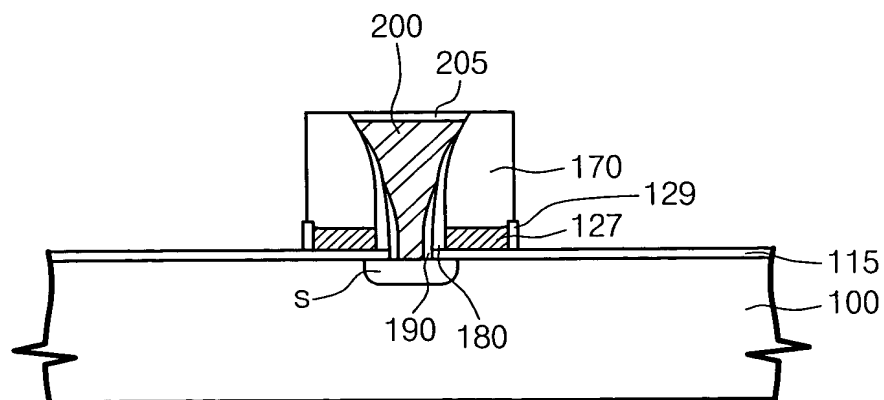


Fig. 11

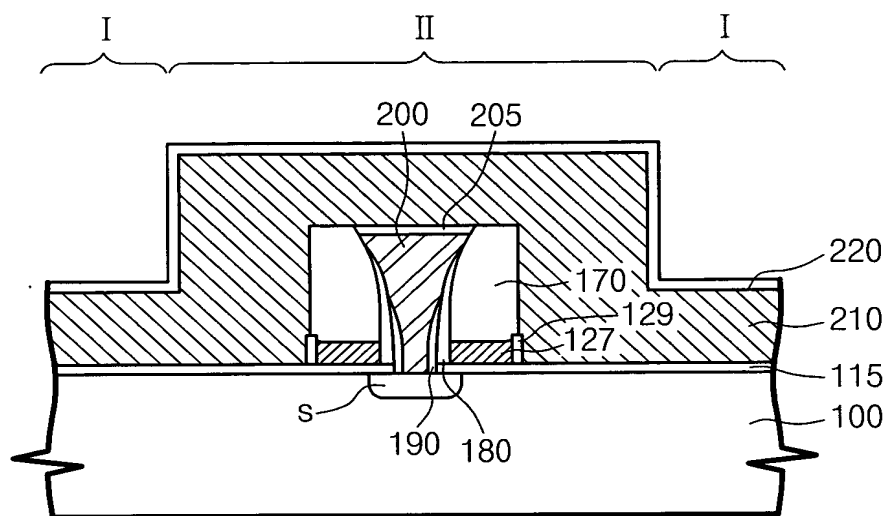
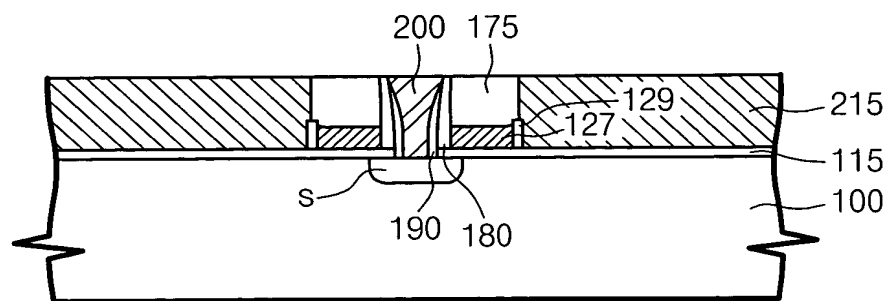


Fig. 12



A cross-sectional view of a semiconductor device. A central channel region (127) is defined by two side regions (129). The channel region (127) contains a central layer (180) and is flanked by two side layers (190). The side regions (129) contain a central layer (175) and are flanked by two side layers (200). The entire structure is supported by a substrate (100) with a top layer (115). The side regions (129) are separated from the central channel region (127) by a gap (s). The side regions (129) are also separated from the central channel region (127) by a gap (d).